

---

# HB56U264EJN Series

2,097,152-word × 64-bit High Density Dynamic RAM Module

# HITACHI

Under development

---

## Description

The HB56U264EJN belongs to 8 Byte DIMM (Dual In-line Memory Module) family, and has been developed as an optimized main memory solution for 4 and 8 Byte processor applications.

The HB56U264EJN is a 2M × 64 dynamic RAM module, mounted 8 pieces of 16-Mbit DRAM (HM5117805BJ) sealed in SOJ package and 1 pieces of serial EEPROM (24C02) for Presence Detect (PD).

The HB56U264EJN offers Extended Data Out (EDO) Page Mode as a high speed access mode.

An outline of the HB56U264EJN is 168-pin socket type package (dual lead out). Therefore, the HB56U264EJN makes high density mounting possible without surface mount technology. The HB56U264EJN provides common data inputs data outputs. Decoupling capacitors are mounted beneath each SOJ on the module board.

## Features

- 168-pin socket type package (Dual lead out)
  - Lead pitch: 1.27 mm
- Single 5 V (±5%) supply.
- High speed
  - Access time:  $t_{RAC} = 60/70/80$  ns (max)
  - Access time:  $t_{CAC} = 15/18/20$  ns (max)
- Low power dissipation
  - Active mode: 5.1/4.7/4.2 W (max)
  - Standby mode (TTL): 84 mW (max)
  - Standby mode (CMOS): 42 mW (max)
- EDO page mode capability
- 2,048 refresh cycle: 32 ms

Note: This document contains information on a product under development. Hitachi reserves the right to change or discontinue the product without notice.

# HB56U264EJN Series

- 3 variations of refresh
  - RAS-only refresh
  - CAS-before-RAS refresh
  - Hidden refresh
- TTL compatible

## Ordering Information

Type No.	Access time	Package	Contact pad
HB56U264EJN-6B	60 ns	168-pin dual lead out socket type	Gold
HB56U264EJN-7B	70 ns		
HB56U264EJN-8B	80 ns		

## Pin Arrangement

